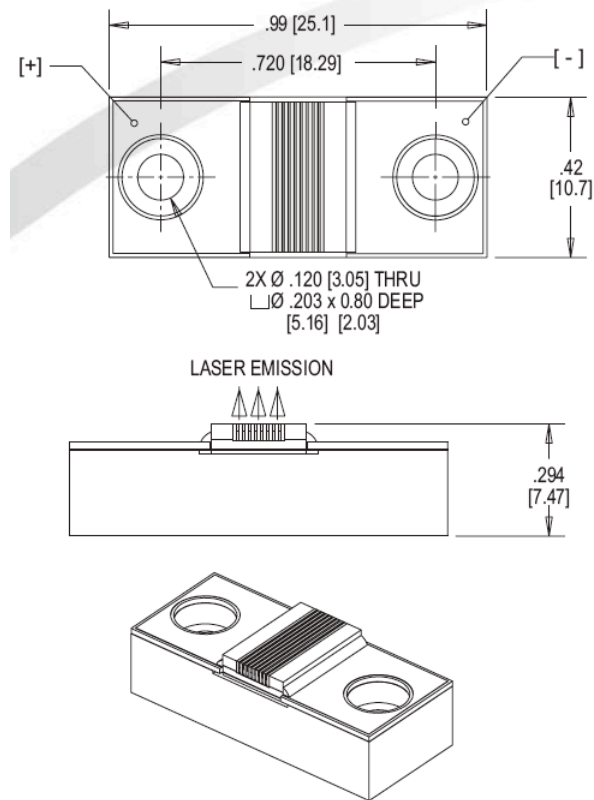


NNG09278349Q

Technical Specs: The Laser Diode Arrays (LDAs) in this procurement must meet the following specifications:

Item 1 – G-3 InAlGaAs laser diode array

- a. Three (3) bar diode array
- b. Peak power per bar: 100W
- c. Peak power per array/stack: 300W
- d. Center wavelength: 885nm (+/- 3nm)
- e. Spectral Width: <3nm FWHM
- f. Bar Pitch: ~400um
- g. Operating Temperature: ~25C
- h. Intended operational condition: QCW mode, 2% duty cycle at 200  $\mu$ s pulse width
- i. All arrays/stacks ordered must be within 1nm of each other (+/- 0.5nm) in order to operate at a common center wavelength at a common heat sink temperature
- j. These LDAs shall be used for drop-in replacements of previously purchased LDAs. We required that the packaging be exactly the same so no modification on the existing hardware will be done. Refer to the mechanical drawing below for further details.



Item 2 – G-8 InAlGaAs laser diode array

- a. Eight (8) bar diode array
- b. Peak power per bar: 100W
- c. Peak power per array/stack: 800W
- d. Center wavelength: 885nm (+/- 3nm)
- e. Spectral Width: <3nm FWHM
- f. Bar Pitch: ~400um
- g. Operating Temperature: ~25C
- h. Intended operational condition: QCW mode, 2% duty cycle at 200  $\mu$ s pulse width
- i. All arrays/stacks ordered must be within 1nm of each other (+/- 0.5nm) in order to operate at a common center wavelength at a common heat sink temperature
- j. These LDAs shall be used for drop-in replacements of previously purchased LDAs. We required that the packaging be exactly the same so no modification on the existing hardware will be done. Refer to the mechanical drawing below for further details.

